



18NM100SZ

Preliminary

POWER MOSFET

18A, 1000V N-CHANNEL SUPER-JUNCTION MOSFET

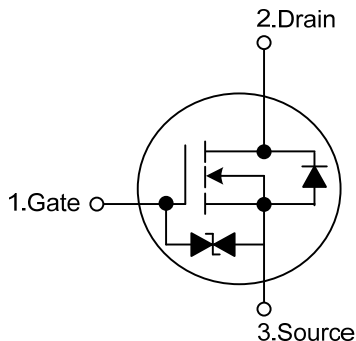
DESCRIPTION

The UTC **18NM100SZ** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

FEATURES

- * $R_{DS(ON)} \leq 0.43 \Omega @ V_{GS}=10V, I_D=6.0A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness
- * With ESD protection

SYMBOL

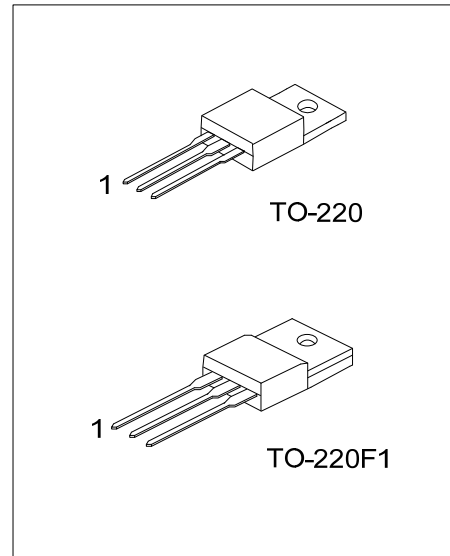


ORDERING INFORMATION

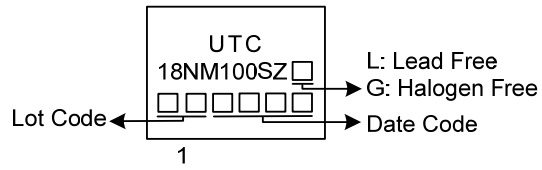
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
18NM100SZL-TA3-T	18NM100SZG-TA3-T	TO-220	G	D	S	Tube
18NM100SZL-TF1-T	18NM100SZG-TF1-T	TO-220F1	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>18NM100SZG-TA3-T</p>	<p>(1) T: Tube</p> <p>(2) TA3: TO-220, TF1: TO-220F1</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING



■ ABSOLUTE MAXIMUM RATING ($T_C=25^\circ\text{C}$ unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	1000	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	18	A
	Pulsed (Note 2)	I_{DM}	54	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	650	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	0.97	V/ns
Power Dissipation	TO-220	P_D	125	W
	TO-220F1		34	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature Range		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 100\text{mH}$, $I_{AS} = 3.6\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$.

4. $I_{SD} \leq 18\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	θ_{JC}	1	$^\circ\text{C}/\text{W}$
	TO-220F1		3.6	$^\circ\text{C}/\text{W}$

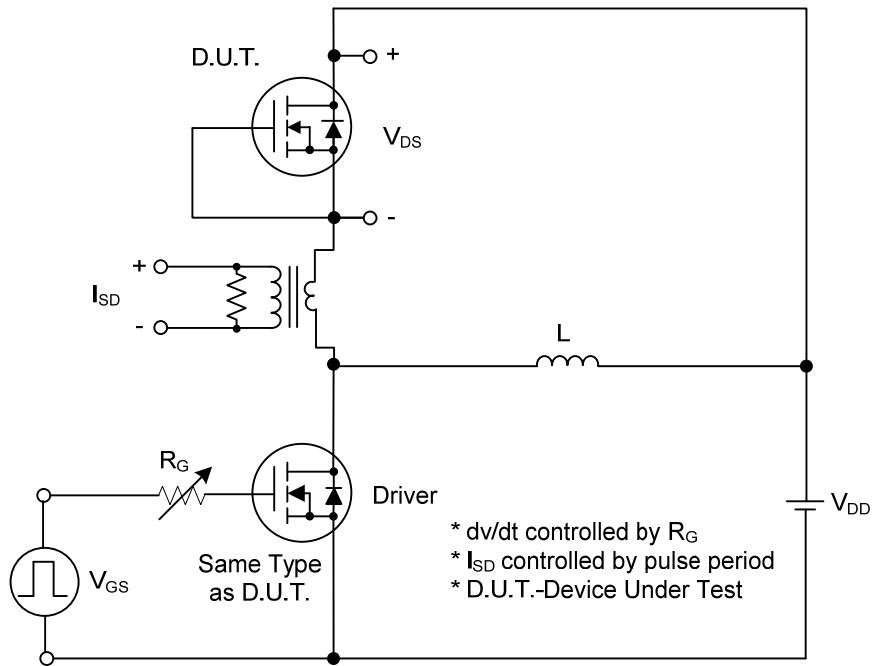
■ ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	1000			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =1000V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS} V _{GS} =+20V, V _{DS} =0V			+10	μA
	Reverse		V _{GS} =-20V, V _{DS} =0V			-10
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =6.0A			0.43	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =50V, f=1.0MHz		1600		pF
Output Capacitance	C _{OSS}			96		pF
Reverse Transfer Capacitance	C _{RSS}			3		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q _G	V _{DS} =760V, V _{GS} =10V, I _D =18A (Note 1, 2)		45		nC
Gate to Source Charge	Q _{GS}			12		nC
Gate to Drain Charge	Q _{GD}			11		nC
Turn-ON Delay Time	t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =18A, R _G =25Ω (Note 1, 2)		16		ns
Rise Time	t _r			22		ns
Turn-OFF Delay Time	t _{D(OFF)}			120		ns
Fall-Time	t _f			53		ns
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I _S				18	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				54	A
Diode Forward Voltage	V _{SD}	I _F =18A, V _{GS} =0V			1.4	V
Reverse Recovery Time	t _{rr}	I _S =18A, V _{GS} =0V, dI _F /dt = 100 A/μs		560		ns
Reverse Recovery Charge (Note 1)	Q _{rr}				11.3	

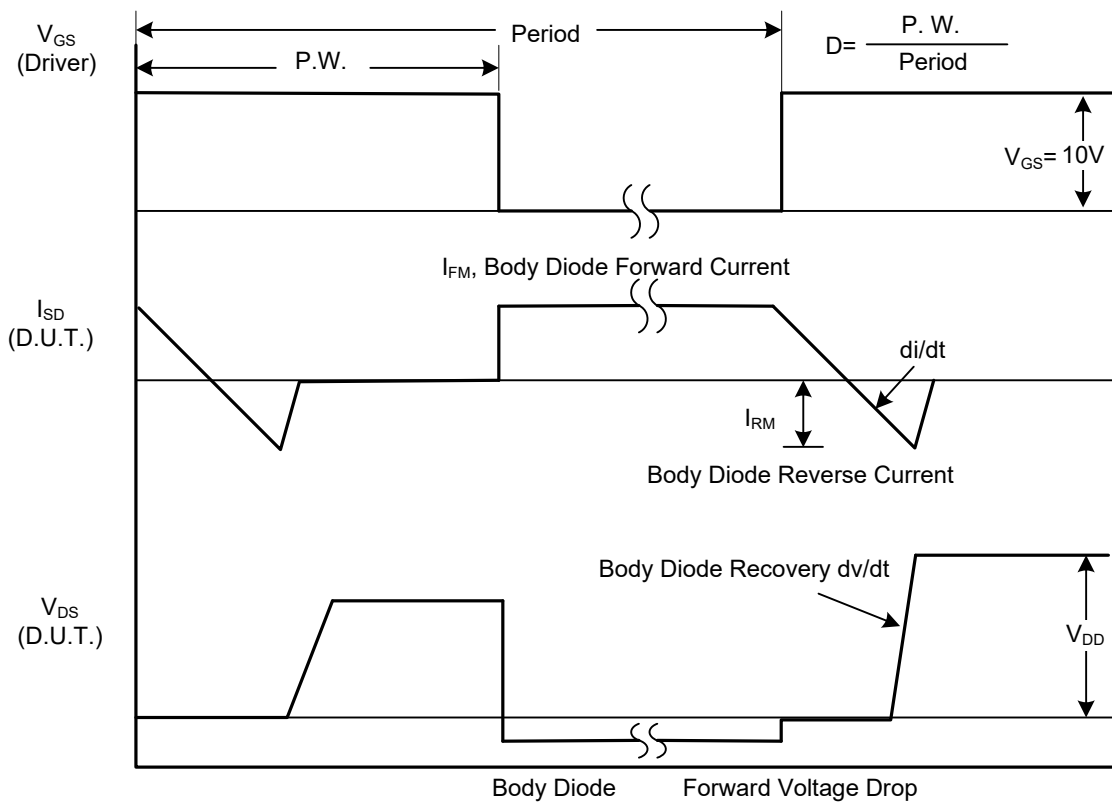
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

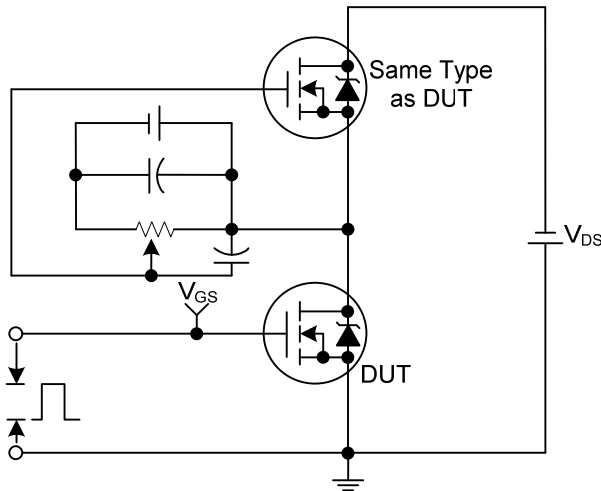


Peak Diode Recovery dv/dt Test Circuit

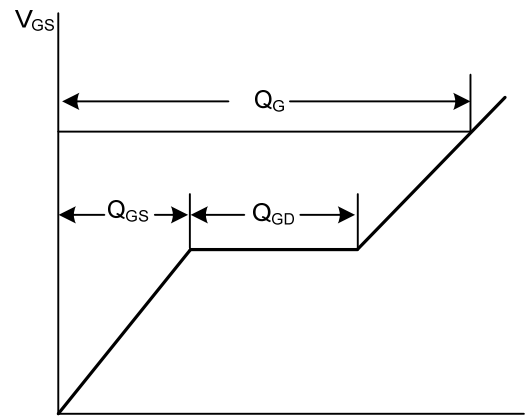


Peak Diode Recovery dv/dt Waveforms

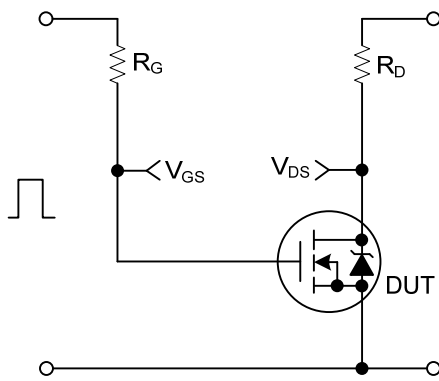
■ TEST CIRCUITS AND WAVEFORMS



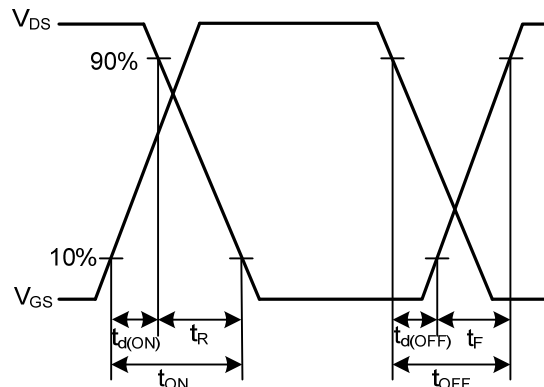
Gate Charge Test Circuit



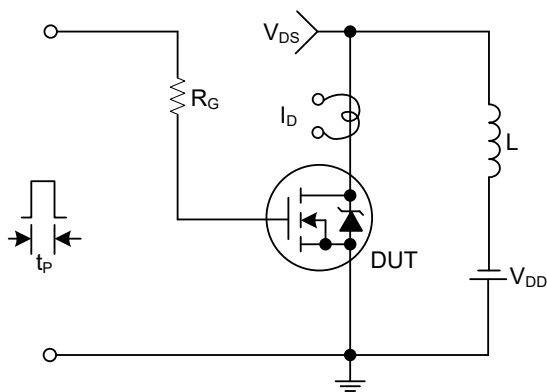
Gate Charge Waveforms



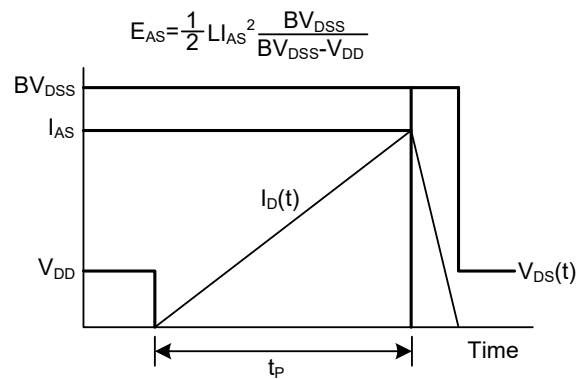
Resistive Switching Test Circuit



Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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